Silicon Diffused Power Transistor BU1706A

GENERAL DESCRIPTION

Enhanced performance, new generation, high-voltage, high-speed switching npn transistor in a plastic envelope intended for use in high frequency electronic lighting ballast applications.

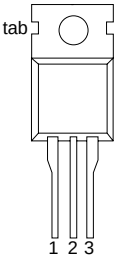
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0 V	-	1750	V
V_{CEO}	Collector-emitter voltage (open base)		-	850	V
I_C	Collector current (DC)		-	5	A
I_{CM}	Collector current peak value		-	8	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25$ ˚C	-	100	W
V_{CEsat}	Collector-emitter saturation voltage	I_C = 1.5 A; I_B = 0.3 A	-	1.0	V
I_{Csat}	Collector saturation current		1.5	-	A
t_f	Fall time	I_{CM} = 1.5 A; $I_{B(on)}$ = 0.3 A	0.25	0.6	µs

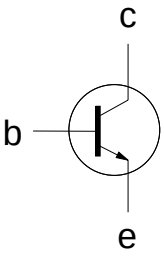
PINNING - TO220AB

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0 V	-	1750	V
V_{CEO}	Collector-emitter voltage (open base)		-	850	V
I_C	Collector current (DC)		-	5	A
I_{CM}	Collector current peak value		-	8	A
I_B	Base current (DC)		-	3	A
I_{BM}	Base current peak value		-	5	A
$-I_{B(AV)}$	Reverse base current	average over any 20ms period	-	100	mA
$-I_{BM}$	Reverse base current peak value		-	4	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25$ ˚C	-	100	W
T_{stg}	Storage temperature		-65	150	˚C
T_j	Junction temperature		-	150	˚C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Junction to mounting base		-	1.25	K/W
$R_{th\ j\text{-}a}$	Junction to ambient	in free air	60	-	K/W

STATIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	Collector cut-off current [1]	V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$	-	-	1.0	mA
I_{CES}		V_{BE} = 0 V; V_{CE} = 1500 V	-	-	20	µA
I_{CES}		V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$; T_j = 125 ˚C	-	-	2.0	mA
I_{EBO}	Emitter cut-off current	V_{EB} = 12 V; I_C = 0 A	-	-	1	mA
$V_{CEOsust}$	Collector-emitter sustaining voltage	I_B = 0 A; I_C = 100 mA; L = 25 mH	750	-	-	V
V_{CEsat}	Collector-emitter saturation voltage	I_C = 1.5 A; I_B = 0.3 A	-	-	1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C = 1.5 A; I_B = 0.3 A	-	-	1.3	V
h_{FE}	DC current gain	I_C = 5 mA; V_{CE} = 10 V	8	-	-	
h_{FE}		I_C = 400 mA; V_{CE} = 3 V	12	18	35	
h_{FE}		I_C = 1.5 A; V_{CE} = 1 V	5	7	-	

DYNAMIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (resistive load)	I_{Con} = 1.5 A; I_{Bon} = -I_{Boff} = 0.3 A			
t_{on}	Turn-on time		1.1	1.5	µs
t_s	Turn-off storage time		5	6.5	µs
t_f	Turn-off fall time		0.75	1.0	µs
	Switching times (inductive load)	I_{Con} = 1.5 A; I_{Bon} = 0.3 A; L_B = 1 µH; -V_{BB} = 5 V			
t_s	Turn-off storage time		2.0	3.0	µs
t_f	Turn-off fall time		0.25	0.6	µs
	Switching times (inductive load)	I_{Con} = 1.5 A; I_{Bon} = 0.3 A; L_B = 1 µH; -V_{BB} = 5 V; T_j = 100 ˚C			
t_s	Turn-off storage time		2.2	3.3	µs
t_f	Turn-off fall time		0.2	0.7	µs

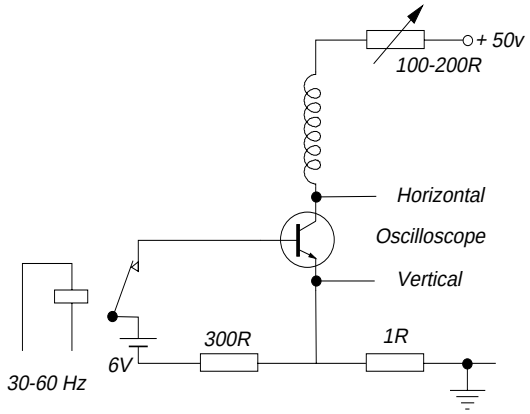


Fig.1. Test circuit for $V_{CEOsust}$.

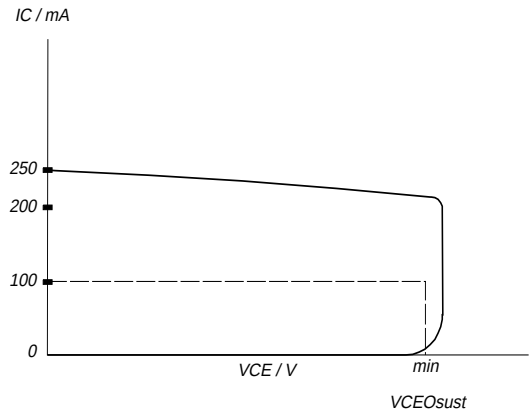


Fig.2. Oscilloscope display for $V_{CEOsust}$.

1 Measured with half sine-wave voltage (curve tracer).

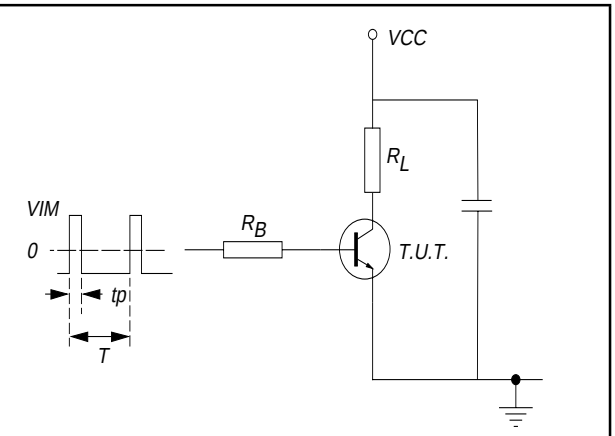


Fig.3. Test circuit resistive load. V_{IM} = -6 to +8 V
V_{CC} = 250 V; tp = 20 μs; δ = tp / T = 0.01.
R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

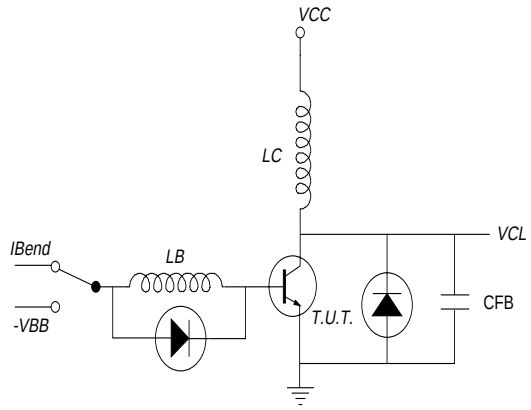


Fig.6. Test Circuit RBSOA.
V_{CC} = 150 V; $-V_{BB}$ = 5 V; L_C = 2 mH; $V_{CL} \leq$ 1500 V;
L_B = 1 μH

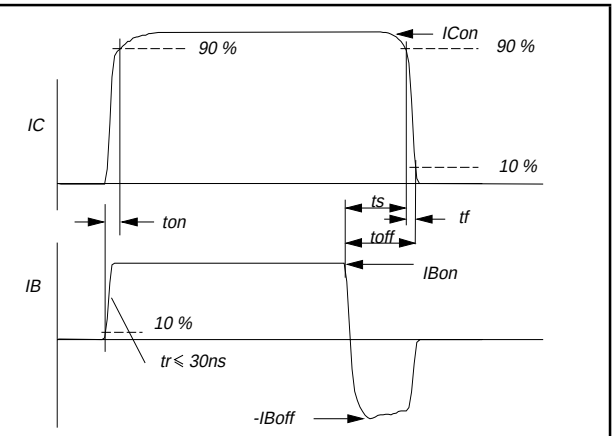


Fig.4. Switching times waveforms with resistive load.

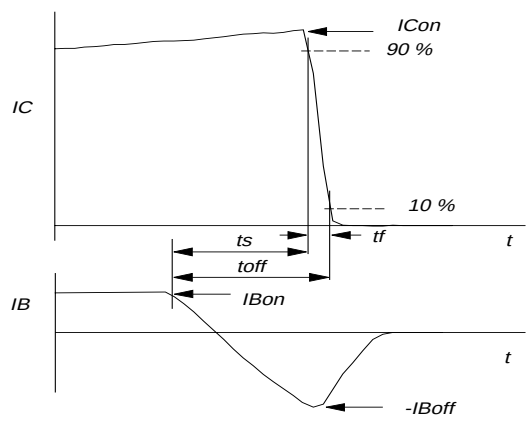


Fig.7. Switching times waveforms with inductive load.

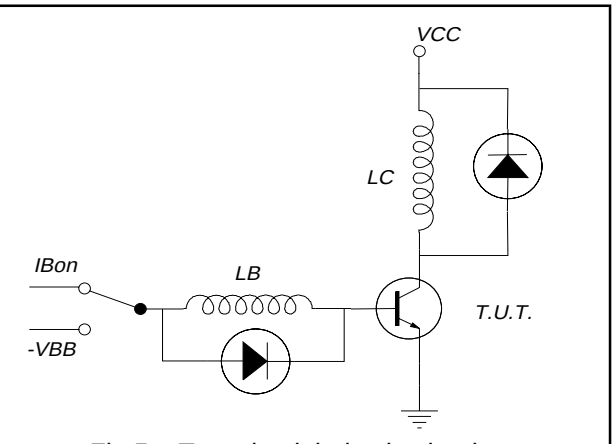


Fig.5. Test circuit inductive load.
V_{CC} = 300 V; $-V_{BE}$ = 5 V; L_B = 1 uH

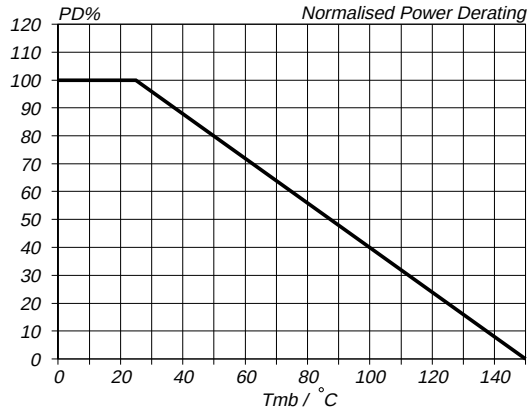


Fig.8. Normalised power dissipation.
PD% = 100·PD/PD $_{25\,°C}$ = f (T_{mb})

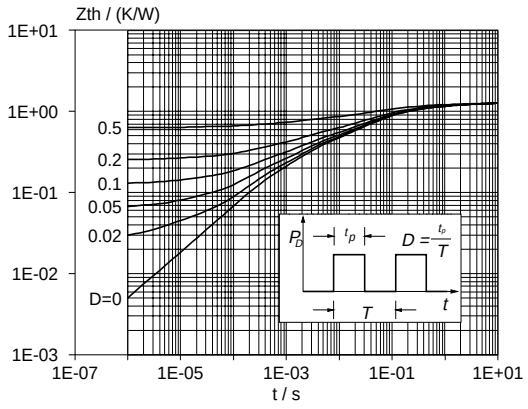


Fig.9. Transient thermal impedance.
$Z_{th\ j\text{-}mb} = f(t)$; parameter $D = t_p/T$

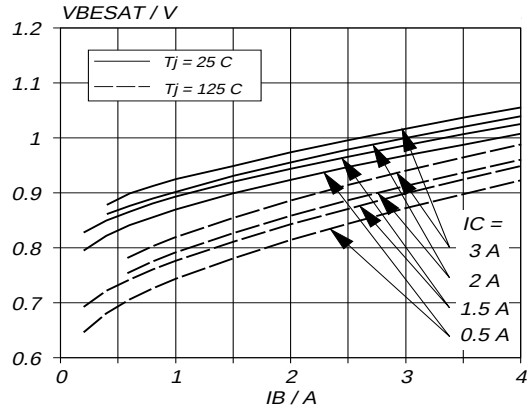


Fig.12. Typical base-emitter saturation voltage.
$V_{BEsat} = f(I_B)$; parameter I_C

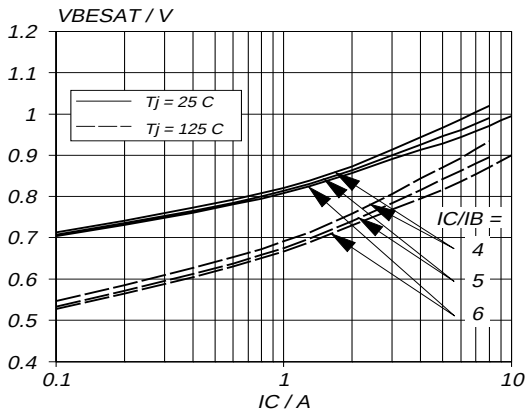


Fig.10. Typical base-emitter saturation voltage.
$V_{BEsat} = f(I_C)$; parameter I_C/I_B

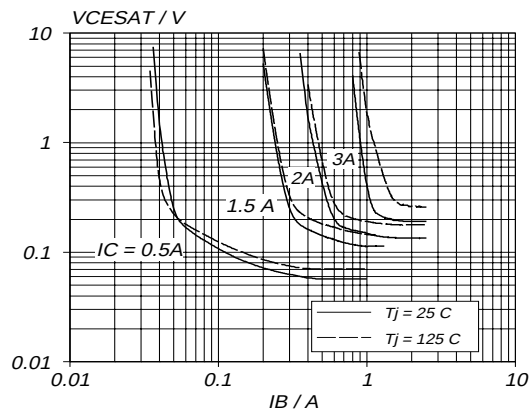


Fig.13. Typical collector-emitter saturation voltage.
$V_{CEsat} = f(I_B)$; parameter I_C

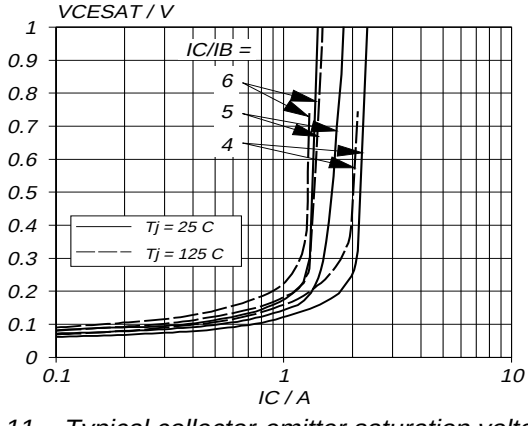


Fig.11. Typical collector-emitter saturation voltage.
$V_{CEsat} = f(I_C)$; parameter I_C/I_B

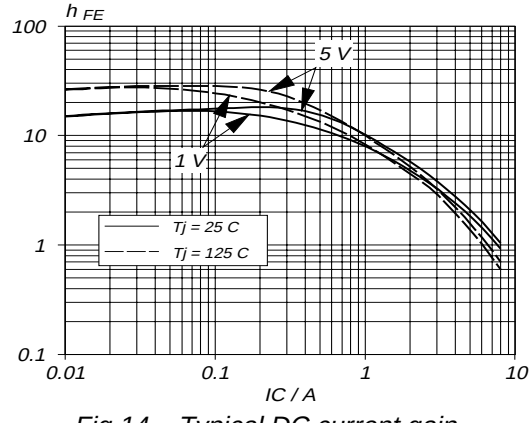


Fig.14. Typical DC current gain.
$h_{FE} = f(I_C)$; parameter V_{CE}

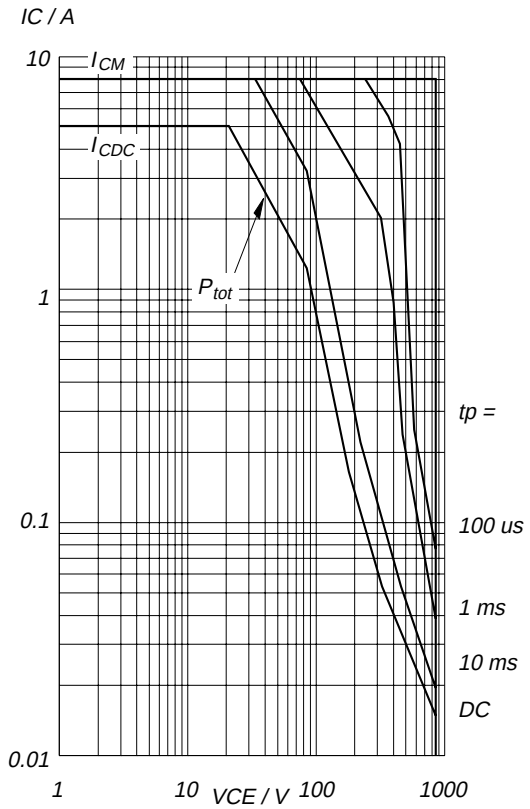


Fig.15. Forward bias safe operating area. T_{mb} = 25 ˚C

I Region of permissible DC operation.
II Extension for repetitive pulse operation.
NB: Mounted with heatsink compound and 30 ± 5 newton force on the centre of the envelope.

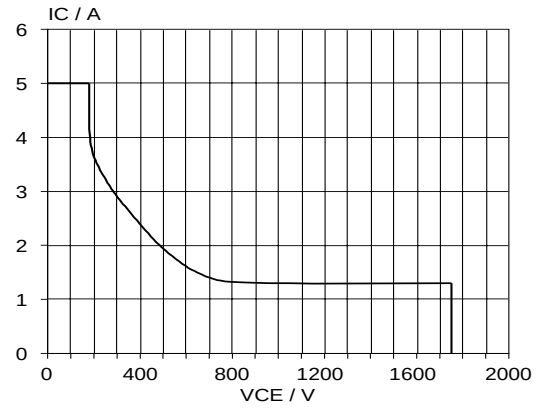


Fig.16. Reverse bias safe operating area. $T_j \leq T_{jmax}$

MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

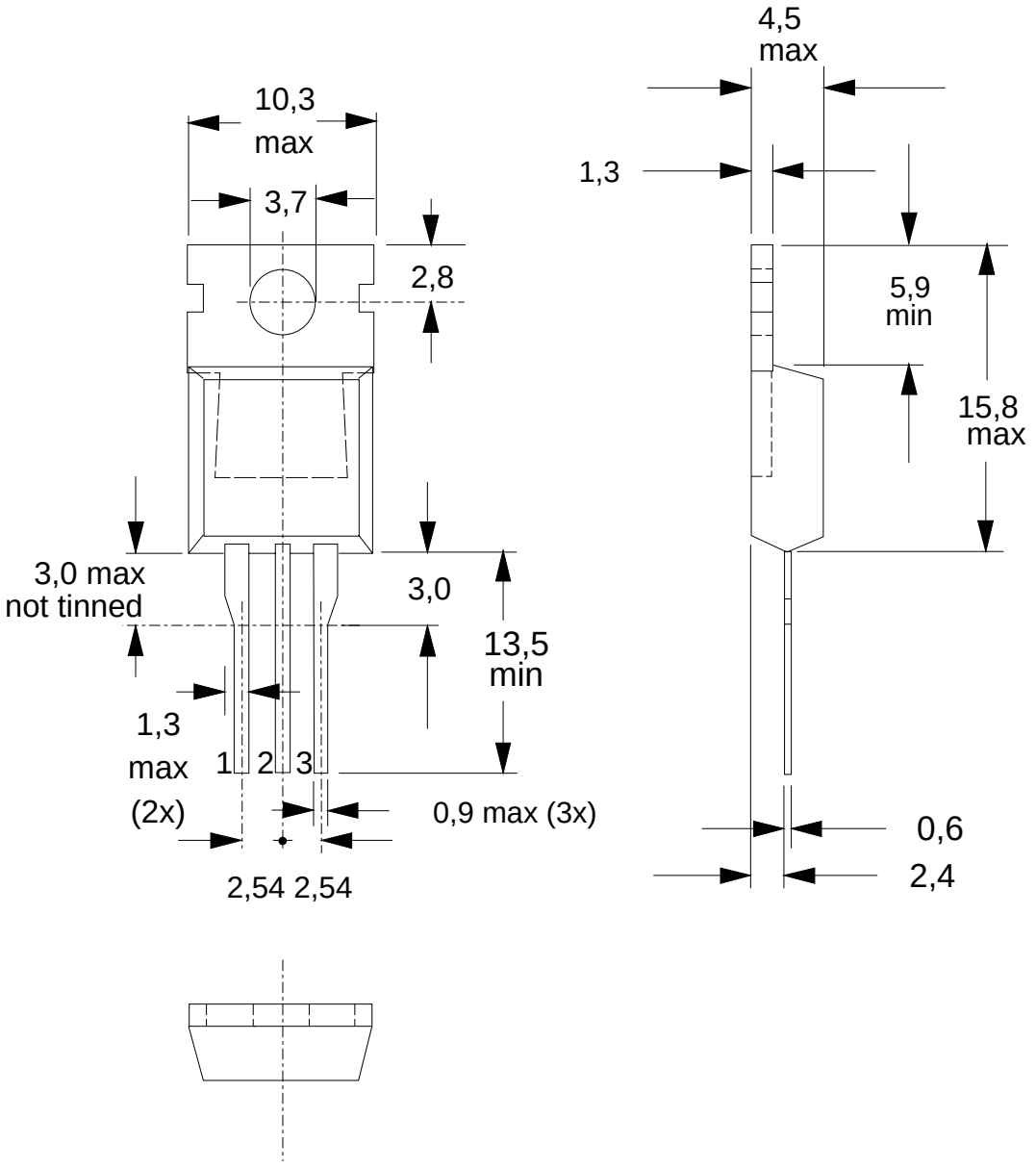


Fig.17. TO220AB; pin 2 connected to mounting base.

Notes
1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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